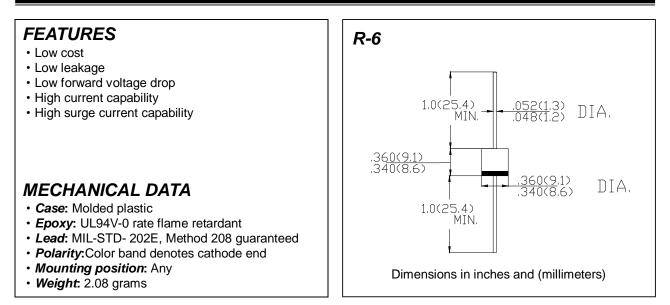
6A05M THRU 6A10M

TECHNICAL SPECIFICATIONS OF SILICON RECTIFIER

VOLTAGE: 50-1000V

CURRENT: 6.0A



MAXIMUM RATINGS AND ELECTRONICAL CHARACTERISTICS

Ratings at 25° C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

		SYMBOL	6A05M	6A1M	6A2M	6A4M	6A8M	6A8M	6A10M	units
Maximum Recurrent Peak Reverse Voltage		V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage		V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage		V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward rectified Current at $T_A=75^{\circ}C$		I _o	6.0							Α
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rate load (JEDEC method)		I _{FSM}	250						Α	
Maximum Instantaneous forward Voltage at 6.0A DC		V _F	1.1							v
Maximum DC Reverse Current at Rated DC Blocking Voltage	@ T _A =25°C		10							μA
	@ T _A =100°C	I _R	500							
Maximum Full Load Reverse Current Average, Full Cycle .375"(9.5mm) lead length at $T_L=75^{\circ}C$			50] .
Typical Junction Capacitance (Note)		CJ	150							pF
Typical Thermal Resistance		$R_{\theta JA}$	10						°C/W	

Notes: Measured at 1MHz and applied reverse voltage of 4.0 volts